



S1FLB, S1FLD, S1FLG, S1FLJ, S1FLM

Vishay Semiconductors

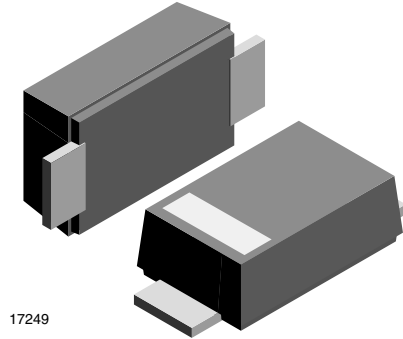
Small Signal Switching Diode, High Voltage

Features

- For surface mounted applications
- Low profile package
- Ideal for automated placement
- Glass passivated
- High temperature soldering: 260 °C/10 s at terminals
- Wave and reflow solderable
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC



RoHS COMPLIANT



17249

Mechanical Data

Case: JEDEC DO219AB (SMF[®]) plastic case

Polarity: band denotes cathode end

Weight: approx. 15 mg

Packaging codes/options:

GS18/10K per 13" reel (8 mm tape), 50K/box

GS08/3K per 7" reel (8 mm tape), 30K/box

Parts Table

| Part | Ordering code | Marking | Remarks |
|-------|--------------------------|---------|---------------|
| S1FLB | S1FLB-GS18 or S1FLB-GS08 | FB | Tape and reel |
| S1FLD | S1FLD-GS18 or S1FLD-GS08 | FD | Tape and reel |
| S1FLG | S1FLG-GS18 or S1FLG-GS08 | FG | Tape and reel |
| S1FLJ | S1FLJ-GS18 or S1FLJ-GS08 | FJ | Tape and reel |
| S1FLM | S1FLM-GS18 or S1FLM-GS08 | FM | Tape and reel |

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

| Parameter | Test condition | Part | Symbol | Value | Unit |
|---|----------------|-------|------------------|-------|------|
| Maximum repetitive peak reverse voltage | | S1FLB | V _{RRM} | 100 | V |
| | | S1FLD | V _{RRM} | 200 | V |
| | | S1FLG | V _{RRM} | 400 | V |
| | | S1FLJ | V _{RRM} | 600 | V |
| | | S1FLM | V _{RRM} | 1000 | V |
| Maximum RMS voltage | | S1FLB | V _{RMS} | 70 | V |
| | | S1FLD | V _{RMS} | 140 | V |
| | | S1FLG | V _{RMS} | 280 | V |
| | | S1FLJ | V _{RMS} | 420 | V |
| | | S1FLM | V _{RMS} | 700 | V |
| Maximum DC blocking voltage | | S1FLB | V _{DC} | 100 | V |
| | | S1FLD | V _{DC} | 200 | V |
| | | S1FLG | V _{DC} | 400 | V |
| | | S1FLJ | V _{DC} | 600 | V |
| | | S1FLM | V _{DC} | 1000 | V |

| Parameter | Test condition | Part | Symbol | Value | Unit |
|---|------------------------------|------|-------------|-------|------|
| Maximum average forward rectified current | $T_{tp} = 75\text{ °C}^{1)}$ | | $I_{F(AV)}$ | 1.5 | A |
| | $T_A = 65\text{ °C}^{1)}$ | | $I_{F(AV)}$ | 0.7 | A |
| Peak forward surge current 8.3 ms single half sine-wave | $T_L = 25\text{ °C}$ | | I_{FSM} | 22 | A |

Note:

¹⁾ Averaged over any 20 ms period

Thermal Characteristics

$T_{amb} = 25\text{ °C}$, unless otherwise specified

| Parameter | Test condition | Symbol | Value | Unit |
|--|----------------|----------------|---------------|------|
| Thermal resistance junction to ambient air ¹⁾ | | R_{thJA} | 180 | K/W |
| Operating junction and storage temperature range | | T_j, T_{stg} | - 55 to + 150 | °C |

Note:

¹⁾ Mounted on epoxy substrate with 3 mm x 3 mm Cu pads ($\geq 40\text{ }\mu\text{m}$ thick)

Electrical Characteristics

$T_{amb} = 25\text{ °C}$, unless otherwise specified

| Parameter | Test condition | Symbol | Min. | Typ. | Max. | Unit |
|---|--|----------|------|------|------|---------------|
| Maximum instantaneous forward voltage | $1\text{ A}^{1)}$ | V_F | | | 1.1 | V |
| Maximum DC reverse current at rated DC blocking voltage | $T_A = 25\text{ °C}$ | I_R | | | 10 | μA |
| | $T_A = 125\text{ °C}$ | I_R | | | 50 | μA |
| Reverse recovery time | $I_F = 0.5\text{ A}, I_R = 1\text{ A}, I_{rr} = 0.25\text{ A}$ | t_{rr} | | | 1.8 | μs |
| Typical capacitance at 4 V, MHz | | C_j | | 4 | | pF |

Note:

¹⁾ Pulse test: 300 μ pulse width, 1 % duty cycle

Typical Characteristics

$T_{amb} = 25\text{ °C}$, unless otherwise specified

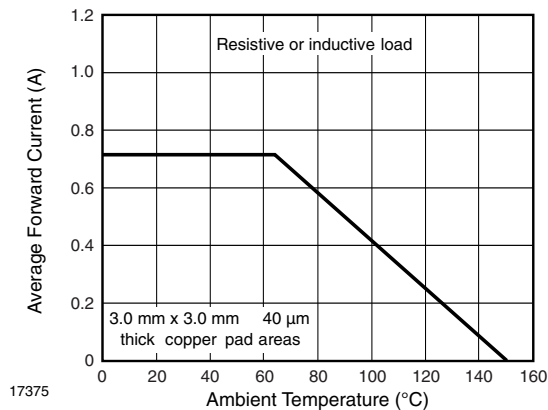


Figure 1. Forward Current Derating Curve

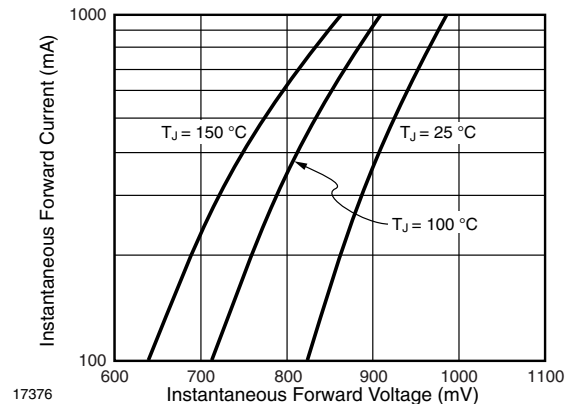


Figure 2. Typical Instantaneous Forward Characteristics

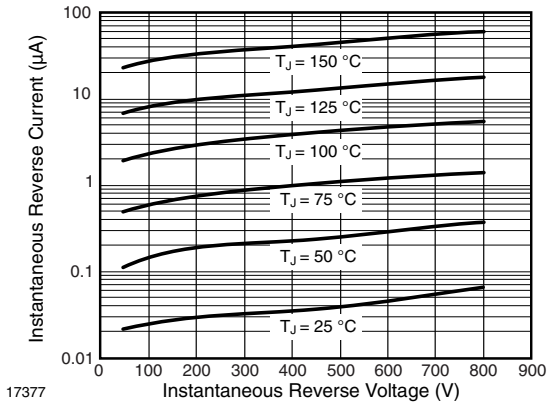


Figure 3. Typical Instantaneous Reverse Characteristics

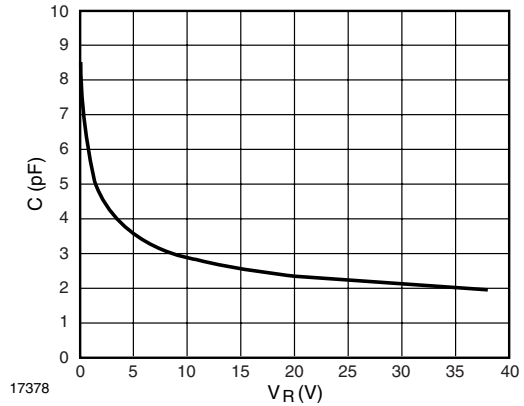
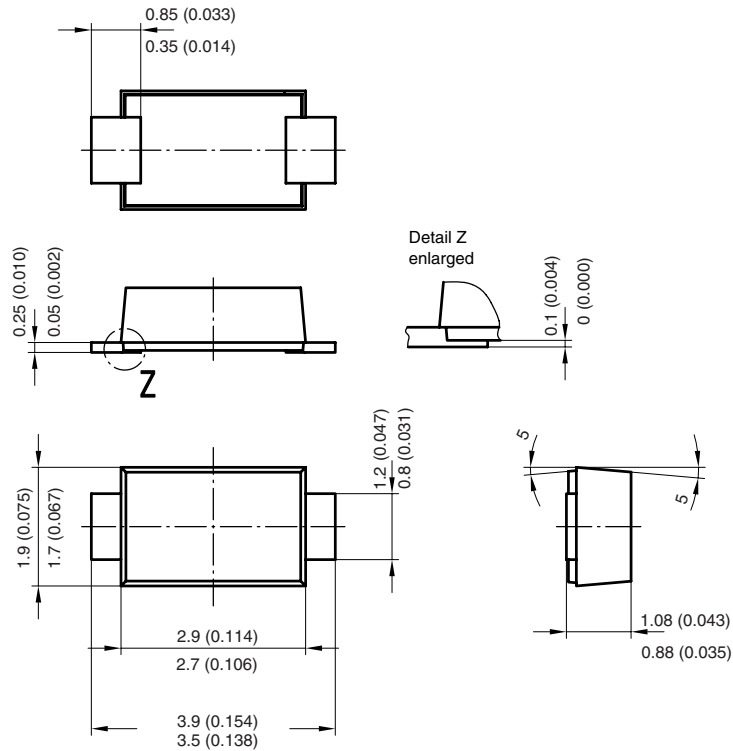
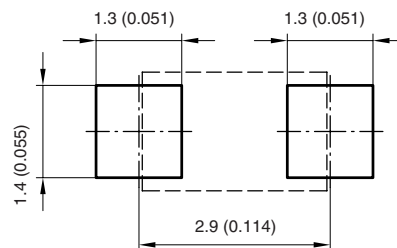


Figure 4. Capacitance vs. Reverse Voltage

Package Dimensions in millimeters (inches): DO219AB



Foot print recommendation:



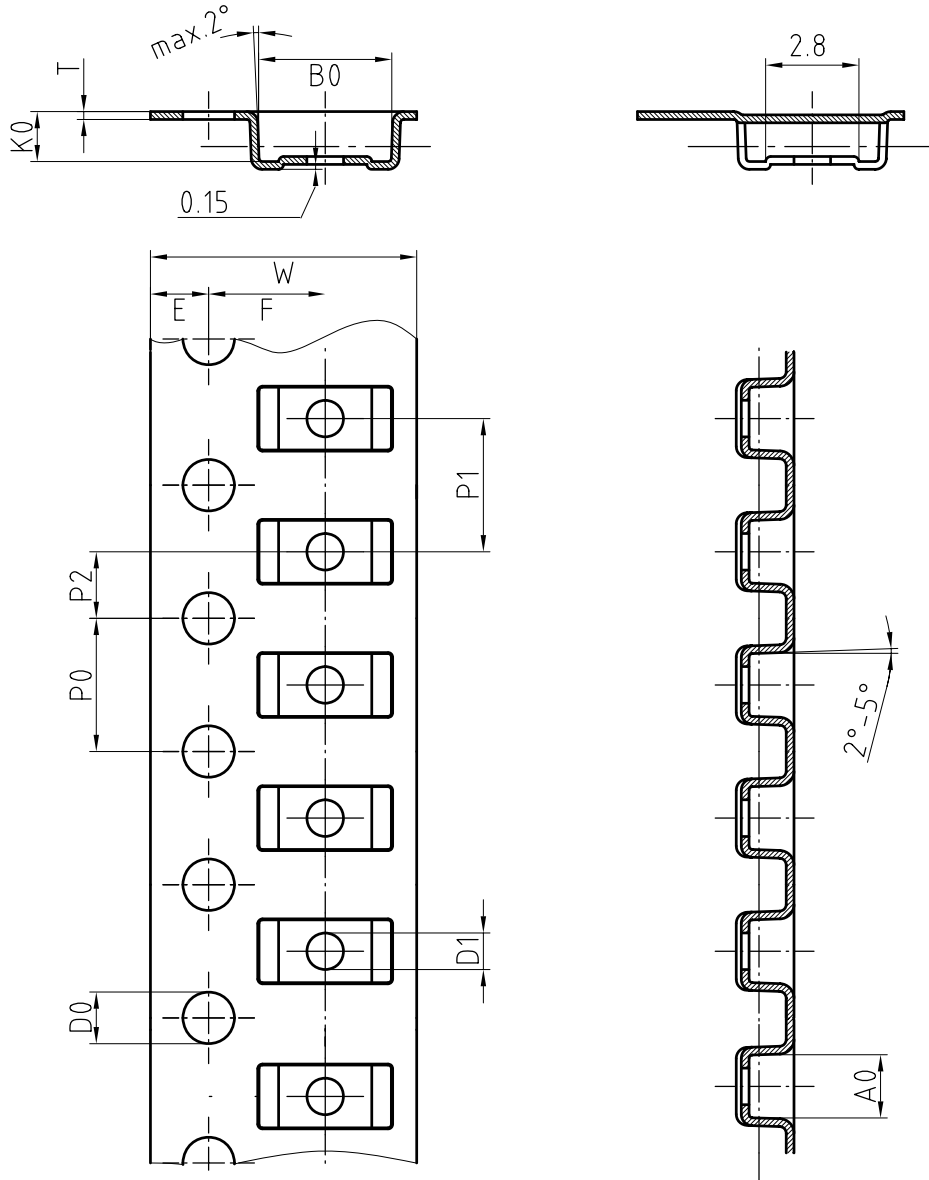
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Blister Tape Dimensions for SMF in millimeters



| Mat: | A0 | B0 | K0 | W | T | P0 | P2 | P1 | D0 | D1 | E | F |
|------|-----|-----|-----|-----|-------|-----|-----|-----|-----|----|------|-----|
| PS | 1.9 | 4.0 | 1.5 | 8.0 | 0.235 | 4.0 | 2.0 | 4.0 | 1.5 | 1 | 1.75 | 3.5 |

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